High Electron Mobility Transistor Market By Type (Gallium Nitride (GaN), Silicon Carbide (SiC), Gallium Arsenide (GaAs), Others), By End User (Consumer Electronics, Automotive, Industrial, Aerospace and Defense, Others): Global Opportunity Analysis and Industry Forecast, 2021-2031

Market Report | 2022-08-01 | 215 pages | Allied Market Research

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Report description:

A high electron mobility transistor (HEMT) is a field effect transistor which incorporates a junction between two types with different band gaps as the channel instead of a doped region. The primary characteristics of a HEMT device includes operation at higher frequencies, and hence it is used in high frequency equipment like mobile phones, satellite television receivers, voltage converters, and radar equipment.

Ample investments and developments on HEMTs by key players is expected to drive the growth of the HEMT market. However, lack of standard techniques to produce and develop HEMT devices is expected to pose major threats for the market. Furthermore, high demand for new HEMT technologies in defense and automotive industry are expected to offer lucrative opportunities for the growth of the global high electron mobility transistor (HEMT) market.

The global high electron mobility transistor (HEMT) market is segmented on the basis of type and end user. By type, the market is divided into gallium nitride (GaN), silicon carbide (SiC), gallium arsenide (GaAs) and others. By end user, the market is analyzed across consumer electronics, automotive, industrial, aerospace & defense and others.

Region wise, the High Electron Mobility Transistor (HEMT) market trends are analyzed across North America (U.S., Canada, and Mexico), Europe (UK, Germany, France, and rest of Europe), Asia-Pacific (China, Japan, India, South Korea, and rest of Asia-Pacific), and LAMEA (Latin America, Middle East, and Africa). North America accounted for the highest share, owing to the expansion of the electronics market and rise in sales of EVs.

The key players operating in the market includes include Infineon, Intel Corporation, Microsemi, Mitsubishi, NXP Semiconductor N.V., Qorvo, Renesas Electronics, ST Microelectronics, Texas Instruments and Wolfspeed are provided in this report.

Key Benefits For Stakeholders

-This report provides a quantitative analysis of the market segments, current trends, estimations, and dynamics of the high electron mobility transistor market analysis from 2021 to 2031 to identify the prevailing high electron mobility transistor market opportunities.
-The market research is offered along with information related to key drivers, restraints, and opportunities.
-Porter's five forces analysis highlights the potency of buyers and suppliers to enable stakeholders make profit-oriented business decisions and strengthen their supplier-buyer network.
-In-depth analysis of the high electron mobility transistor market segmentation assists to determine the prevailing market opportunities.
-Major countries in each region are mapped according to their revenue contribution to the global market.
-Market player positioning facilitates benchmarking and provides a clear understanding of the present position of the market players.
-The report includes the analysis of the regional as well as global high electron mobility transistor market trends, key players, market segments, application areas, and market growth strategies.
Key Market Segments
By Type
- Gallium Nitride (GaN)
- Silicon Carbide (SiC)
- Gallium Arsenide (GaAs)
- Others
By End User
- Others
- Consumer Electronics
- Automotive
- Industrial
- Aerospace and Defense
By Region
- North America
- U.S.
- Canada
- Mexico
- Europe
- UK
- Germany
- France
- Rest Of Europe
- Asia-Pacific
- Rest Of Asia-Pacific
- China
- Japan
- India
- South Korea
- LAMEA
- Latin America
- Middle East
- Africa
- Key Market Players
- Qorvo

- Infineon
- Mitsubishi
- Microsemi
- Wolfspeed
- NXP SEMICONDUCTORS
- ST Microelectronics
- Texas Instruments
- Intel Corporation
- Renesas Electronics

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